**Product data sheet** 

## 1. General description

Silicon Carbide Schottky diode in a DFN 8\*8 plastic package, designed for high frequency switched-mode power supplies.



### 2. Features and benefits

- · Highly stable switching performance
- High forward surge capability IFSM
- Extremely fast reverse recovery time
- Superior in efficiency to Silicon Diode alternatives
- Reduced losses in associated MOSFET
- Reduced EMI
- Reduced cooling requirements
- RoHS compliant

### 3. Applications

- · Power factor correction
- Telecom / Server SMPS
- UPS
- PV inverter
- PC Silverbox
- LED / OLED TV
- Motor Drives

### 4. Quick reference data

#### Table 1. Quick reference data

Symbol	Parameter	Conditions	Values			Unit	
Absolute	maximum rating						
$V_{RRM}$	repetitive peak reverse voltage			6	50		V
$I_{F(AV)}$	average forward current	$\delta$ = 0.5 ; square-wave pulse; T <sub>c</sub> ≤ 150 °C; Fig. 1; Fig. 2; Fig. 3	4		А		
T <sub>j</sub>	junction temperature		175		°C		
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static ch	aracteristics			,			
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 4 A; T <sub>j</sub> = 25 °C; <u>Fig. 5</u>		-	1.5	1.7	V
		I <sub>F</sub> = 4 A; T <sub>j</sub> = 150 °C; <u>Fig. 5</u>		-	1.8	2.1	V
Dynamic	characteristics						
$Q_r$	recovered charge	$I_F = 4 \text{ A}$ ; $dI_F/dt = 500 \text{ A/}\mu\text{s}$ ; $V_R = 400 \text{ V}$ ; $T_i = 25 \text{ °C}$ ; Fig. 7		-	7	-	nC

# 5. Pinning information

### **Table 2. Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	n.c.	not connected	[]	K — A
2	n.c.	not connected	5	001aaa020
3	А	anode		
4	Α	anode	ρ,,,	
5	К	mounting base; connected to cathode	1 2 3 4	

# 6. Ordering information

### **Table 3. Ordering information**

Type number	Package name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
WNSC04650T	DFN8*8	WNSC04650T6J	Tape	3000	DFN8X8N	25-Dec-2019

# 7. Marking

### Table 4. Marking codes

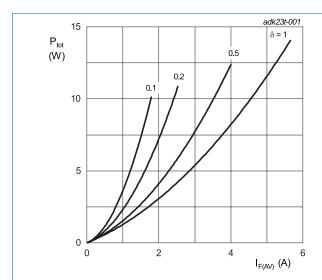
Type number	Marking codes
WNSC04650T	WNSC 04650T

# 8. Limiting values

#### **Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
$V_{RRM}$	repetitive peak reverse voltage		650	V
$V_{RWM}$	crest working reverse voltage		650	V
$V_R$	reverse voltage	DC	650	V
I <sub>F(AV)</sub>	average forward current	$δ$ = 0.5; square-wave pulse; $T_c \le 150$ °C; Fig. 1; Fig. 2; Fig. 3	4	А
I <sub>FRM</sub>	repetitive peak forward current	$\delta$ = 0.5; t <sub>p</sub> = 25 μs; T <sub>c</sub> ≤ 150 °C; square-wave pulse	8	А
I <sub>FSM</sub>	non-repetitive peak	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse	24	Α
	forward current	$t_p$ = 10 μs; $T_{j(init)}$ = 25 °C; square-wave pulse	235	А
l <sup>2</sup> t	I <sup>2</sup> t for fusing	sine-wave pulse; $T_{j(init)} = 25 \text{ °C}$ ; $t_p = 10 \text{ ms}$	3	A <sup>2</sup> s
T <sub>stg</sub>	storage temperature		-55 to 175	°C
T <sub>j</sub>	junction temperature		175	°C



$$\begin{split} I_{F(AV)} &= I_{F(RMS)} \times \sqrt{\delta} \\ V_o &= 1.017 \text{ V; R}_s = 0.2593 \text{ }\Omega \end{split}$$

Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values

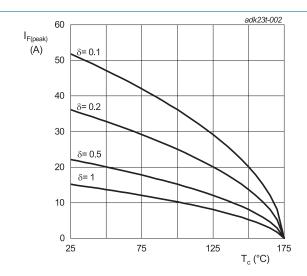


Fig. 2. Current derating as a function of case temperature

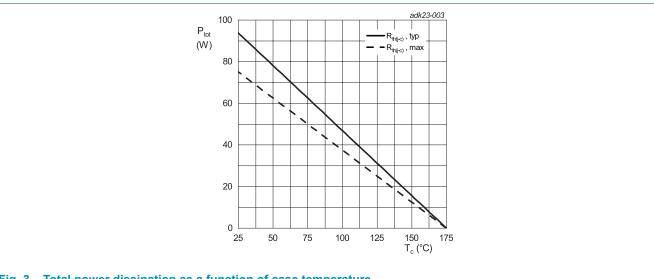
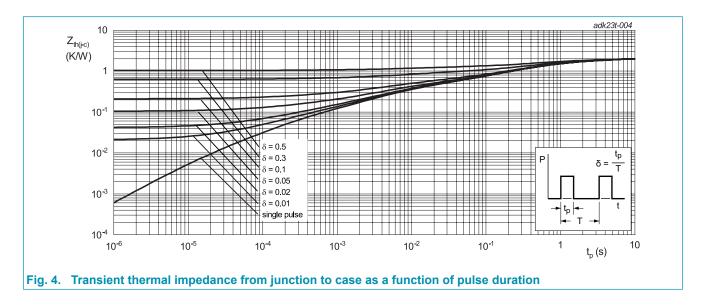


Fig. 3. Total power dissipation as a function of case temperature

### 9. Thermal characteristics

**Table 6. Thermal characteristics** 

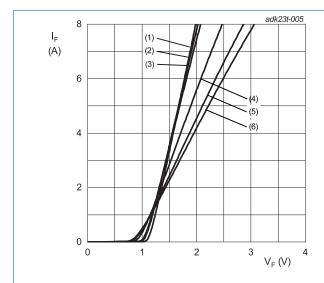
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{\text{th(j-c)}}$	thermal resistance from junction to case	<u>Fig. 4</u>	-	1.6	2	K/W
$R_{\text{th(j-a)}}$	thermal resistance from junction to ambient free air	in free air	-	50	-	K/W



# 10. Characteristics

**Table 7. Characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static cha	racteristics		`			
$V_{F}$	forward current	I <sub>F</sub> = 4 A; T <sub>j</sub> = 25 °C; <u>Fig. 5</u>	-	1.5	1.7	V
		I <sub>F</sub> = 4 A; T <sub>j</sub> = 150 °C; <u>Fig. 5</u>	-	1.8	2.1	V
		I <sub>F</sub> = 4 A; T <sub>j</sub> = 175 °C; <u>Fig. 5</u>		2	2.25	V
I <sub>R</sub>	reverse current	V <sub>R</sub> = 650 V; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>	-		25	μA
		V <sub>R</sub> = 650 V; T <sub>j</sub> = 175 °C; <u>Fig. 6</u>	-		100	μA
Dynamic	characteristics		'			
Q <sub>r</sub>	recovered charge	$I_F = 4 \text{ A}; V_R = 400 \text{ V}; dI_F/dt = 500 \text{ A/}\mu\text{s};$ $T_j = 25 \text{ °C}; Fig. 7$	-	7	-	nC
C <sub>d</sub>	diode capacitance	f = 1 MHz; V <sub>R</sub> = 1 V; T <sub>j</sub> = 25 °C	-	141	-	pF
		f = 1 MHz; V <sub>R</sub> = 300 V; T <sub>j</sub> = 25 °C	-	23	-	pF
		f = 1 MHz; V <sub>R</sub> = 600 V; T <sub>j</sub> = 25 °C	-	22	-	pF
E <sub>as</sub>	non-repetitive avalanche energy	$I_R = 3.5 \text{ A}; L = 5 \text{ mH}; T_{j(init)} = 25 \text{ °C}$	30	-	-	mJ



 $V_o = 1.017 \text{ V}; R_s = 0.2593 \Omega$ (1) T<sub>1</sub> = -55 °C: typical values

(1)  $T_j = -55$  °C; typical values

(2) T<sub>j</sub> = 0 °C; typical values (3) T<sub>j</sub> = 25 °C; typical values

(4)  $T_j = 100 \,^{\circ}\text{C}$ ; typical values

(5)  $T_j = 150$  °C; typical values (6)  $T_j = 175$  °C; typical values

Fig. 5. Forward current as a function of forward voltage; typical values

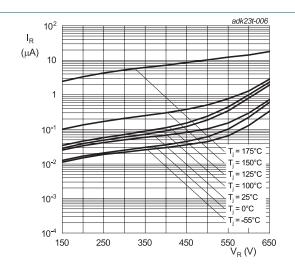


Fig. 6. Reverse leakage current as a function of reverse voltage; typical value

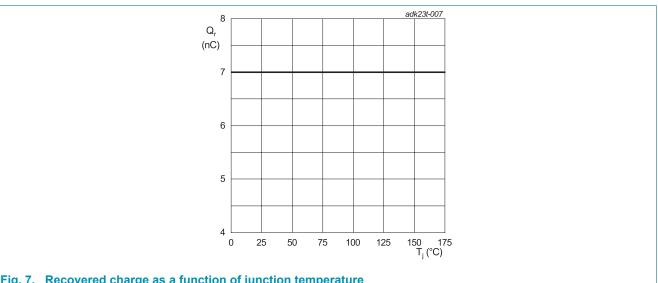
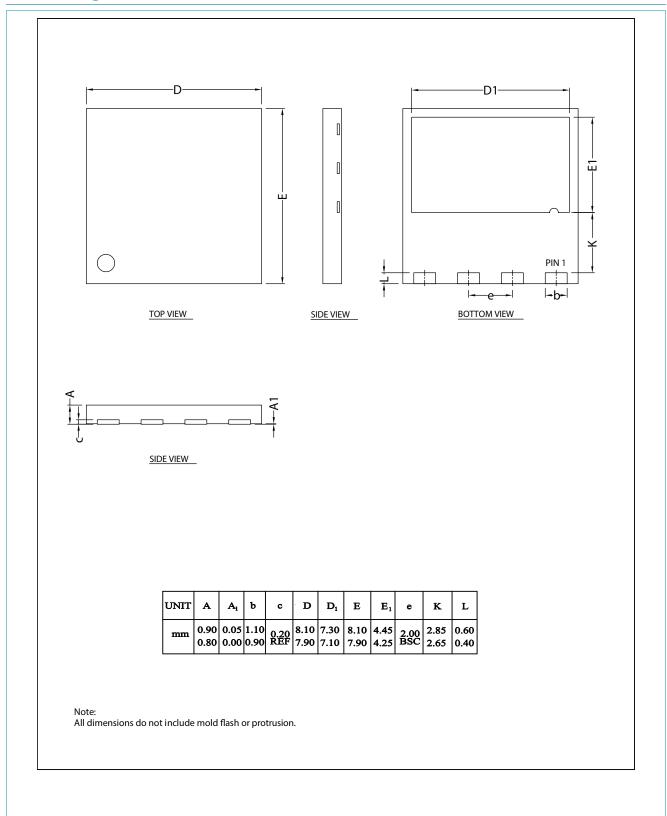


Fig. 7. Recovered charge as a function of junction temperature

# 11. Package outline



### 12. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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